

Cypress Semiconductor Qualification Report

**QTP# 98116 VERSION 1.0
April, 1998**

**UltraLogic™ 32-Macrocell Flash CPLD
CY7C371i**

PRODUCT/TECHNOLOGY INFORMATION

PRODUCT DESCRIPTION (for qualification)			
Qualification Purpose: Qualify 32-Macrocell Flash CPLD, CY7C371i, Rev. E (chop of 128-Macrocell Flash CPLD, CY7C374i/CY7C375i, Rev. E)			
Marketing Part #:	CY7C371i		
Package:	44 pins PLCC		
Device Description:	UltraLogic™ 32-Macrocell Flash CPLD		
Cypress Division:	Cypress Semiconductor Corporation - PLD Division		
Overall Die (or Mask) REV Level (pre-requisite for qualification):	Rev. E		
Die Size (stepping):	231 mils x 86 mils	What ID markings on Die:	7C371i

TECHNOLOGY/FAB PROCESS DESCRIPTION - FLASH28			
Number of Metal Layers:	2	Metal Composition:	Metal 1: 6,800Å AL-1%Si/1,200Å TiW Metal 2: 1500Å TiW/10,000Å Al-1%Si/300Å Tiw
Passivation Type and Materials:	3,000A SiO ₂ + 15,000A Oxynitride		
Free Phosphorus contents in top glass layer(%):	None		
Die Coating(s), if used:	None		
Generic Process Technology/Design Rule (μ-drawn):	CMOS FLASH 0.65μm		
Gate Oxide Material/Thickness (MOS):	Gox1 = 225Å, Gox2 = 165Å, Tunel ox = 100Å		
Name/Location of Die Fab (prime) Facility:	Cypress Semiconductor - Round Rock, TX		
Die Fab Line ID/Wafer Process ID:	Fab 2 / FLASH28		

PACKAGE/ASSEMBLY INFORMATION

PLASTIC PACKAGE/ASSEMBLY DESCRIPTION			
Package Outline, Type, or Name:	44-pin Plastic Leaded Chip Carrier (PLCC)		
Mold Compound Name/Manufacturer:	Nitto-MP8000		
Lead Frame material:	Copper		
Lead Finish, composition:	Solder Plated, 85%Sn, 15%Pb		
Die Attach Area Plating:	Silver Spot		
Die Attach Method:	Paste	Die Attach Material:	Silver Epoxy
Wire Bond Method:	Thermosonic	Wire Material/Size:	Gold / 1.3 mil
JESD22-A112 Moisture Sensitivity Level	Level 1		
Assembly Line ID and Process ID:	Cypress Bangkok, Thailand		

Note: Please contact a Cypress Representative for other packages availability.

RELIABILITY TESTS PERFORMED

Stress/Test	Test Condition (Temp/Bias)	Result P/F
High Temperature Operating Life Early Failure Rate	Dynamic Operating Condition, Vcc = 5.75V, 150°C	P
High Temperature Operating Life Latent Failure Rate	Dynamic Operating Condition, Vcc = 5.75V, 150°C	P
Read and Record Life Test	Dynamic Operating Condition, Vcc = 5.75V, 150°C	P
High Temperature Steady State Life	Static Operating Condition, Vcc = 5.75V, 125°C	P
High Accelerated Saturation Test (HAST)	140°C, 85%RH, 5.5V Precondition: JESD22 Moisture Sensitivity Level 1 (168 Hrs , 85/85%RH)	P
Temperature Cycle (Plastic device)	MIL-STD-883C, Method 1010, Condition C, -65°C to 150°C Precondition: JESD22 Moisture Sensitivity Level 1 (168 Hrs , 85/85%RH)	P
C-SAM	Cypress Spec. 25-00104	P
Data Bake-Plastic	165°C, no bias	P
Electrostatic Discharge Human Body Model (ESD-HBM)	MIL-STD-883, Method 3015.7	2,200V
Electrostatic Discharge Charge Device Model (ESD-CDM)	Cypress Spec. 25-00020	500V
Latchup Sensitivity	In accordance with JEDEC 17. Cypress Spec. 01-00081	
Static Latchup		10.2
Dynamic Latchup		7.7V

RELIABILITY FAILURE RATE SUMMARY

Stress/Test	Device Tested/ Device Hours	# Fail s	Activatio n Energy	Therma l AF⁴	Failure Rate³
High Temperature Operating Life Early Failure Rate	528 Devices	0	N/A	N/A	0 PPM
High Temperature Operating Life ^{1,2} Long Term Failure Rate	59,500 DHRs	0	0.7	170	91 FIT

- ¹ Assuming an ambient temperature of 55°C and a junction temperature rise of 15°C.
² Chi-squared 60% estimations used to calculate the failure rate.
³ Failure rate estimates do not include the voltage acceleration factor.
⁴ Thermal Acceleration Factor is calculated from the Arrhenius equation.

$$AF = \exp \left[\frac{E_A}{k} \left[\frac{1}{T_2} - \frac{1}{T_1} \right] \right]$$

where:

E_A = The Activation Energy of the defect mechanism.
 k = Boltzmann's constant = 8.62x10⁻⁵ eV/Kelvin.
 T₁ is the junction temperature of the device under stress and T₂ is the junction temperature of the device at use conditions.

RELIABILITY TEST DATA

QTP#: 98116

DEVICE	ASSY-LOC	FABLOT#	ASSYLOT#	DURATION	S/S	REJ	FAIL MODE
STRESS: DATA BAKE-PLASTIC (165C, NO BIAS)							
CY7C371I-JC	ALPHA-X	2740074	219711475	168	85	0	
CY7C371I-JC	ALPHA-X	2740074	219711475	552	85	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE (150C, 5.75V)							
CY7C371I-JC	ALPHA-X	2740074	219711475	48	528	0	
STRESS: ESD-CHARGE DEVICE MODEL, 500V							
CY7C371I-JC	ALPHA-X	2803994	219801255	COMP	3	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2200V							
CY7C371I-JC	ALPHA-X	2803994	219801255	COMP	3	0	
STRESS: HI-ACCEL SATURATION TEST (140C, 5.5V), PRECOND. 168 HRS 85C/85%RH							
CY7C371I-JC	ALPHA-X	2740074	219711475	128	50	0	
STRESS: HIGH TEMP STEADY STATE LIFE TEST (125C, 5.75V)							
CY7C371I-JC	ALPHA-X	2740074	219711475	80	85	0	
CY7C371I-JC	ALPHA-X	2740074	219711475	168	85	0	
CY7C371I-JC	ALPHA-X	2740074	219711475	336	85	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE (150C, 5.75V)							
CY7C371I-JC	ALPHA-X	2740074	219711475	80	119	0	
CY7C371I-JC	ALPHA-X	2740074	219711475	500	119	0	
STRESS: READ & RECORD LIFE TEST (150C, 5.75V)							
CY7C371I-JC	ALPHA-X	2740074	219711475	48	12	0	
CY7C371I-JC	ALPHA-X	2740074	219711475	80	12	0	
CY7C371I-JC	ALPHA-X	2740074	219711475	500	12	0	
STRESS: TC COND. C, -65 TO 150C, PRECOND. 168 HRS 85C/85%RH							
CY7C371I-JC	ALPHA-X	2740074	219711475	300	50	0	
CY7C371I-JC	ALPHA-X	2740074	219711475	1000	50	0	

DEVICE RELATED RELIABILITY TEST DATA

QTP#: 97301¹/97305²/97373³

EVAL #	DEVICE	ASSY-LOC	ASSYLOT#	FABLOT#	ACTUAL	TIME	S/S	Ver.	
					TEMP /VOLT	POINT		Rej	Fail Mode
STRESS: DATA BAKE-HERMETIC (250C, NO BIAS)									
97301	CY7C374I-YC	ALPHA-X	219613131	2630682	250C /N/A	96	79	0	

STRESS: DATA BAKE-PLASTIC (165C, NO BIAS)									
97301	CY7C374I-JC	KOREA-A	349611720	2629610	165C /N/A	168	79	0	
97301	CY7C374I-JC	KOREA-A	349611720	2629610	165C /N/A	552	79	0	

STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE (125C, 5,75V)									
97301	CY7C374I-YC	ALPHA-X	219613131	2630682	125C /6.50V	12	167	0	
97301	CY7C374I-YC	ALPHA-X	219613131	2630682	125C /6.50V	48	167	0	
97301	CY7C374I-JC	ALPHA-X	219701981	2636449	125C /6.5V	48	184	0	
97305	CY7C374I-JC	ALPHA-X	219705498	2715844	125C /6.5V	48	500	0	
97301	CY7C374I-JC	KOREA-A	349611720	2629610	125C /6.50V	12	144	0	
97301	CY7C374I-JC	KOREA-A	349611720	2629610	125C /6.50V	48	173	0	

STRESS: ESD-CHARGE DEVICE MODEL									
97305	CY7C374I-JC	ALPHA-X	219705498	2715844	N/A /500V	COMP	3	0	
97301	CY7C375I-AC	KOREA-Q	349612770	2630660	N/A /500V	COMP	3	0	

STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015									
97301	CY7C374I-YC	ALPHA-X	219613131	2630682	N/A /2200V	COMP	3	0	
97305	CY7C374I-JC	ALPHA-X	219705498	2715844	N/A /4400V	COMP	3	0	

STRESS: GROUP C, SUBGROUP 1, LIFE TEST (150C, 5.75V)									
97301	CY7C374I-YMB	ALPHA-X	219613132	2630682	150C /5.75V	184	50	0	

STRESS: HI-ACCEL SATURATION TEST (140C, 5.5V), PRECOND. 192 HRS 30C/60%RH									
97301	CY7C374I-JC	KOREA-A	349611720	2629610	140C /5.5V	128	48	0	
97301	CY7C375I-AC	KOREA-Q	619700713	2645516	130C /5.5V	128	48	0 2 EOS	

STRESS: HIGH TEMP STEADY STATE LIFE TEST (125C, 5.75V)									
97301	CY7C374I-JC	KOREA-A	349611720	2629610	125C /5.75V	336	79	0	
97301	CY7C374I-JC	KOREA-A	349611720	2629610	125C /5.75V	168	79	0	

¹ QTP 97301, UltraLogic 128 Macrocell Flash CPLD, CY7C374i/CY7C375i (Rev. E), Flash 28 Process, Fab 2 qualification.

² QTP 97305, UltraLogic 128 Macrocell Flash CPLD, CY7C374i/CY7C375i (Rev. E), Flash 28 Process, Fab 2 qualification with 14 layer mask fix for erase and soft programming.

³ QTP 97373, UltraLogic 128 Macrocell Flash CPLD, CY7C374i/CY7C375i (Rev. E), Flash 28 Process, Fab 2 qualification with FIT rate improved.

DEVICE RELATED RELIABILITY TEST DATA

QTP#: 97301/97305/97373

EVAL #	DEVICE	ASSY-LOC	ASSYLOT#	FABLOT#	ACTUAL TEMP /VOLT	TIME POINT	S/S	Ver. Rej	Fail	Mode
=====	=====	=====	=====	=====	=====	=====	=====	=====	=====	=====
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE (125C, 5,75V)										
97301	CY7C374I-YC	ALPHA-X	219613131	2630682	125C /6.50V	80	76	0		
97301	CY7C374I-YC	ALPHA-X	219613131	2630682	125C /6.50V	500	76	0		
97301	CY7C374I-JC	ALPHA-X	219701981	2636449	125C /6.5V	500	183	1	1	NON-VISUAL
97305	CY7C374I-JC	ALPHA-X	219705498	2715844	125C /6.5V	80	80	0		
97305	CY7C374I-JC	ALPHA-X	219705498	2715844	125C /6.5V	500	74	0	6	EOS
97373	CY7C374I-JC	ALPHA-X	2199709954P	2722822	125C /5.75V	1000	174	0		
97301	CY7C374I-JC	KOREA-A	349611720	2629610	125C /6.50V	80	77	0		
97301	CY7C374I-JC	KOREA-A	349611720	2629610	125C /6.50V	500	76	0	1	EOS

STRESS: PROGRAM VERIFICATION										
97301	CY7C374I-JC	KOREA-A	349611720	2629610	N/A /N/A	200CY	48	0		

STRESS: READ & RECORD LIFE TEST (150C, 5.75V)										
97301	CY7C374I-JC	KOREA-A	349611720	2629610	150C /6.50V	500	10	0		

STRESS: READ & RECORD LIFE TEST (125C, 5.75V)										
97305	CY7C374I-JC	ALPHA-X	219705498	2715844	125C /6.5V	80	10	0		
97305	CY7C374I-JC	ALPHA-X	219705498	2715844	125C /6.5V	500	10	0		

STRESS: DYNAMIC LATCH-UP TESTING										
97301	CY7C375I-AC	KOREA-Q	349612770	2630660	N/A /10.57V DATA		3	0		

STRESS: TC COND. C, -65 TO 150C, HERMETIC DEVICES										
97301	CY7C374I-YC	ALPHA-X	219613131	2630682	150C /-65C	100	49	0		
97301	CY7C374I-YC	ALPHA-X	219613131	2630682	150C /-65C	1000	49	0		

STRESS: TC COND. C, -65 TO 150C, PRECOND. 192 HRS 30C/60%RH										
97301	CY7C374I-JC	KOREA-A	349611720	2629610	150C /-65C	300	48	0		
97301	CY7C374I-JC	KOREA-A	349611720	2629610	150C /-65C	1000	48	0		
97301	CY7C375I-AC	KOREA-Q	619700713	2645516	150C /-65C	300	50	0		
97301	CY7C375I-AC	KOREA-Q	619700713	2645516	150C /-65C	1000	50	0		
